

SILICON EPITAXIAL PLANAR DIODE

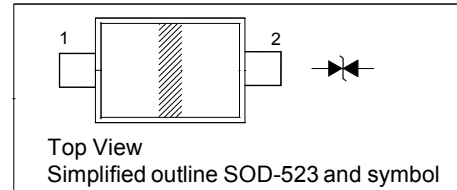
ESD protection diode

Features

- Ultra small mold type
- Bi-direction high reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



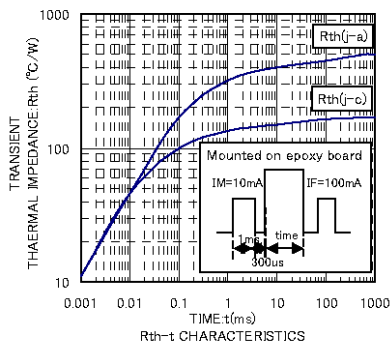
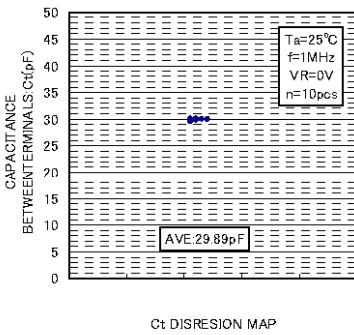
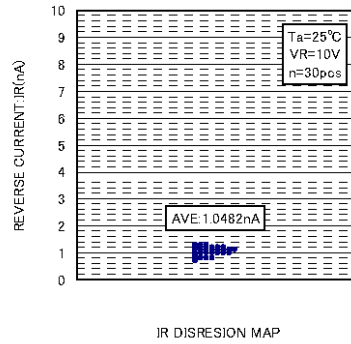
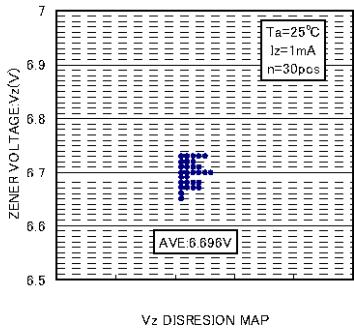
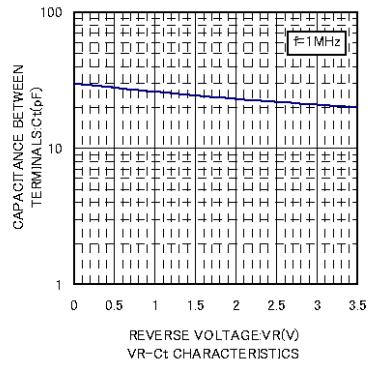
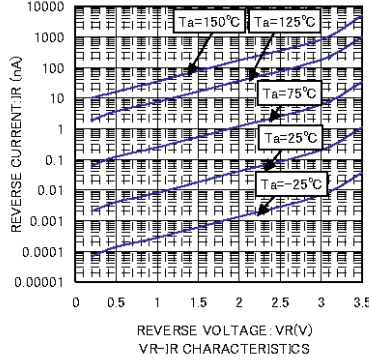
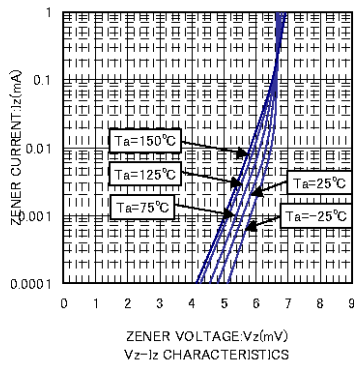
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Pulse Power ($t_p = 10 \times 1000\ \mu\text{s}$)	P_{PK}	10	W
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$
Operation Temperature Range	T_{opr}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Zener Voltage at $I_Z = 1\ \text{mA}$	V_Z	5.5	8	V
Reverse Current at $V_R = 3.5\ \text{V}$	I_R	-	0.01	μA
Capacitance between Terminals at $V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_T	-	30	pF
ESD Voltage Capability (Contact Discharge Mode) at Discharge Capacitance / Resistance: 150 pF / 330 Ω	-	-	15	KV
ESD Voltage Capability (Air Discharge Mode) at Discharge Capacitance / Resistance: 150 pF / 330 Ω	-	-	25	KV

ESD6V8WT





CHINA BASE
INTERNATIONAL

SOD-523

ESD6V8WT

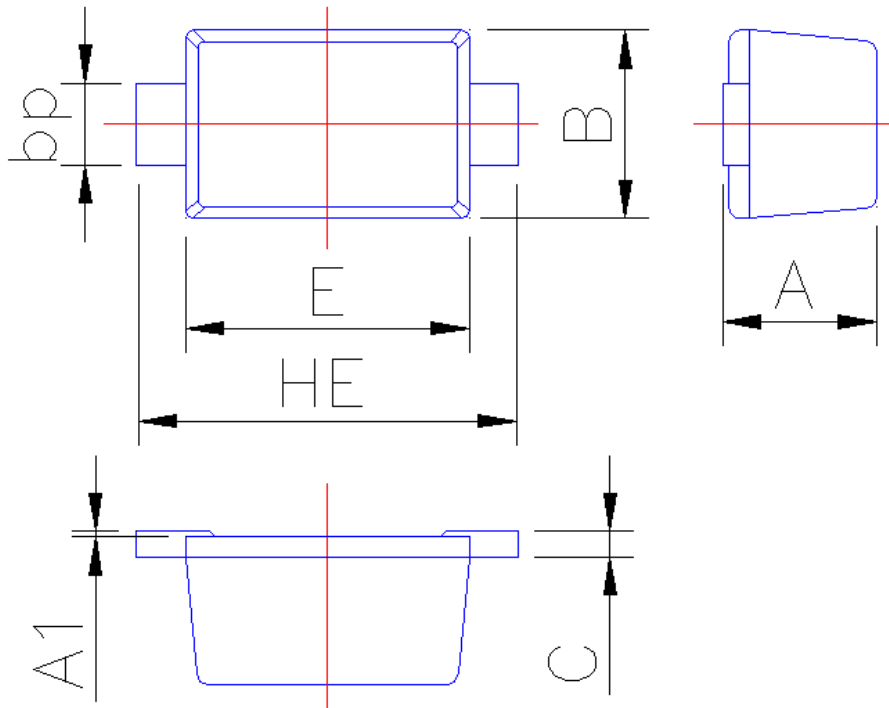


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70